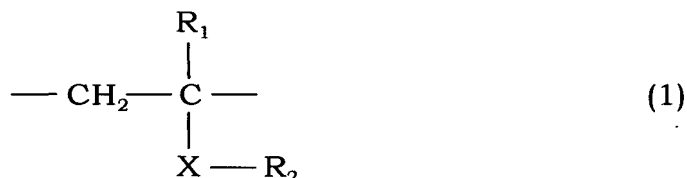


Abstract of the Disclosure

A via-filling material comprising a polymer containing a repeat unit represented by the following formula (1):



wherein  $\text{R}_1$  is a member selected from the group consisting of hydrogen atom, fluorine atom, chlorine atom, bromine atom and methyl group;  $\text{R}_2$  is a member selected from the group consisting of hydrogen atom,  $\text{C}_{1-3}$  alkyl group and  $\text{C}_{1-4}$  alkyl group in which the hydrogen atom is substituted by at least one kind of atoms of fluorine, chlorine and bromine atom; and X is  $\text{---C(=O)O---}$  or  $\text{---S(=O)}_2\text{O---}$  is used as the via-filling material. This via-filling material does not generate deposition around the opening part of a via hole and provides a semiconductor integrated circuit with high reliability even when a trench wider than the via hole is formed by etching the via hole filled with the via-filling material with plasma.